

DS1645EE Partitioned 1024K NV SRAM

FEATURES

- Data retention in the absence of V_{CC}
- · Data is automatically protected during power loss
- Directly replaces 128K x 8 EPROM, EEPROM, or FLASH
- Write protects selected blocks of memory regardless of V_{CC} status when programmed
- Unlimited write cycles
- Low-power CMOS operation
- Over 10 years of data retention
- Standard 32-pin JEDEC pinout
- Available in either 70, 85, or 100 ns read access times
- · Read cycle time equals write cycle time
- Full ±10% operating range
- · Lithium energy source is electrically disconnected to retain freshness until power is applied for the first time.
- Optional industrial temperature range of -40°C to +85°C, designated IND

NC	1	32	V_{CC}	
A16	2	31	WE	
A15	3	30	NC	
A12	4	29	A14	
A7	5	28	A13	
A6	6	27	A8	
A5	7	26	A9	
A4	8	25	A11	
A3	9	24	OE	
A2	10	23	A10	
A1	11	22	CE	
A0	12	21	DQ7	
DQ0	13	20	DQ6	
DQ1	14	19	DQ5	
DQ2	15	18	DQ4	
GND	16	17	DQ3	
32-PIN ENCAPSULATED PACKAGE				

(740 MIL EXTENDED)

PIN DESCRIPTION

PIN ASSIGNMENT

A0 - A16	-	Address Inputs
CE	-	Chip Enable
GND	-	Ground
DQ0 - DQ7	-	Data In/Data Out
V _{CC}	-	Power (+5V)
WE	-	Write Enable
OE	-	Output Enable
NC	-	No Connect

DESCRIPTION

The DS1645EE 1024K Nonvolatile SRAM is a 1,048,576-bit, fully static, nonvolatile SRAM organized as 131,072 words by 8 bits. The DS1645EE has a selfcontained lithium energy source and control circuitry which constantly monitors V_{CC} for an out-of-tolerance condition. When such a condition occurs, the lithium energy source is automatically switched on and write protection is unconditionally enabled to prevent garbled data. In addition the device has the ability to unconditionally write protect blocks of memory so that inadvertent write cycles do not corrupt program and special data space. The nonvolatile static RAM can be used in place of existing 128K x 8 EPROM, EEPROM or FLASH conforming to the popular bytewide 32 pin DIP standard. There is no limit on the number of write cycles which can be executed and no additional support circuitry is required for microprocessor interface. This part is functionally equivalent to the DS1645Y and differs only in pinout. See the DS1645Y/AB 1024K NV SRAM data sheet for technical details.

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